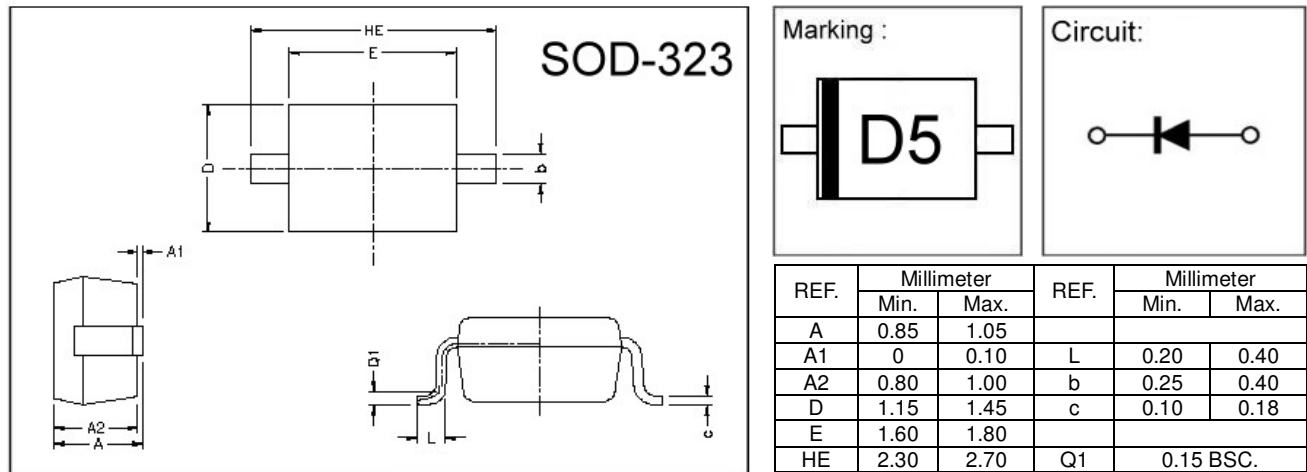


GD511**SURFACE MOUNT, SWITCHING DIODE**
VOLTAGE 85V, CURRENT 0.1A**Description**

The GD511 is designed for ultra high speed switching application, low forward voltage and fast reverse recovery time.

Package Dimensions**Absolute Maximum Ratings at Ta = 25°C**

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Maximum Peak Reverse Voltage	V _{RM}	85	V
Maximum Reverse Voltage	V _R	80	V
Maximum (Peak) Forward Current	I _{FM}	300	mA
Average Forward Current	I _O	100	mA
Surge Current(10ms)	I _{FSM}	2	A
Total Power Dissipation	P _D	150	mW

Electrical Characteristics at Ta = 25°C

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward Voltage	V _F (1)	-	0.6	-	V	I _F =1mA
	V _F (2)	-	0.7	-	V	I _F =10mA
	V _F (3)	-	0.9	1.2	V	I _F =100mA
Reverse Current	I _R	-	-	0.5	μA	V _R =80V
Total Capacitance	C _T	-	2.2	4.0	pF	V _R =0, f=1MHz
Reverse Recovery Time	T _{rr}	-	1.6	4.0	nS	I _F =10mA

Characteristics Curve

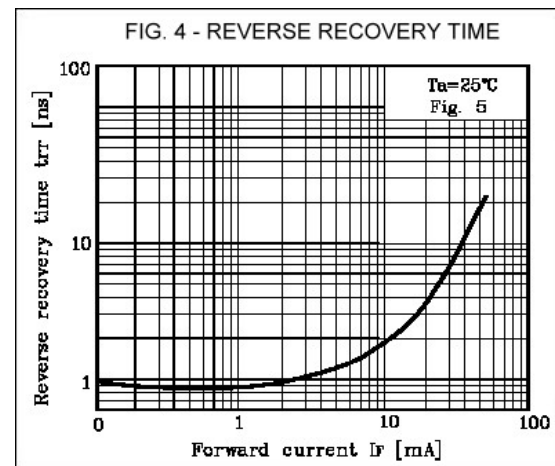
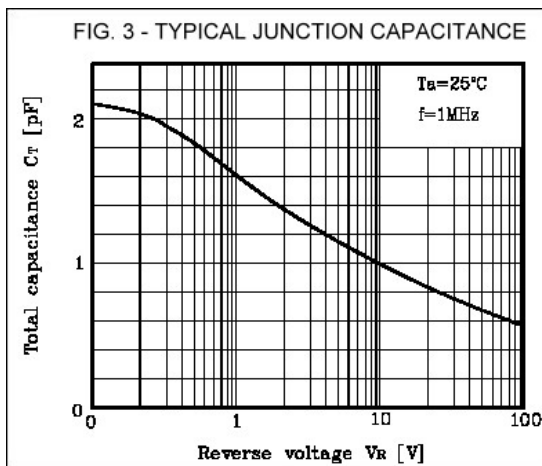
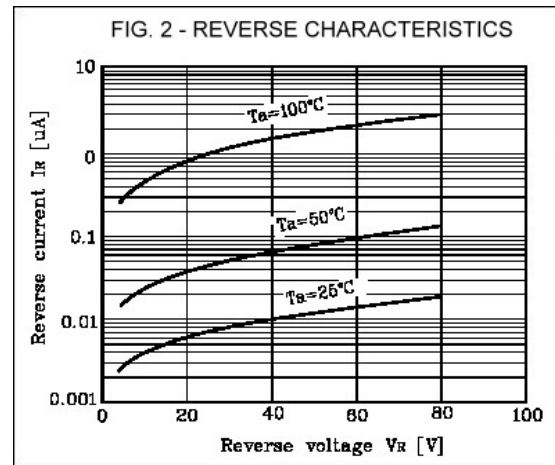
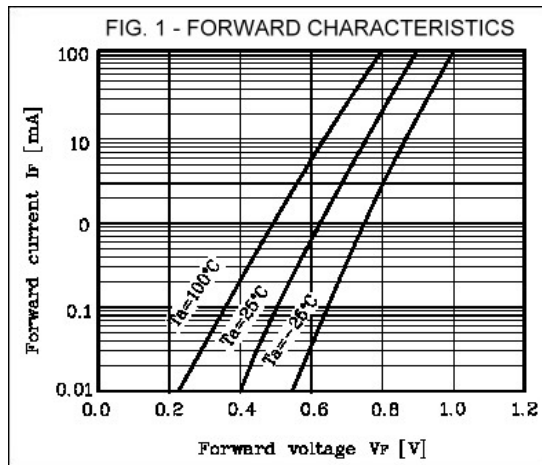
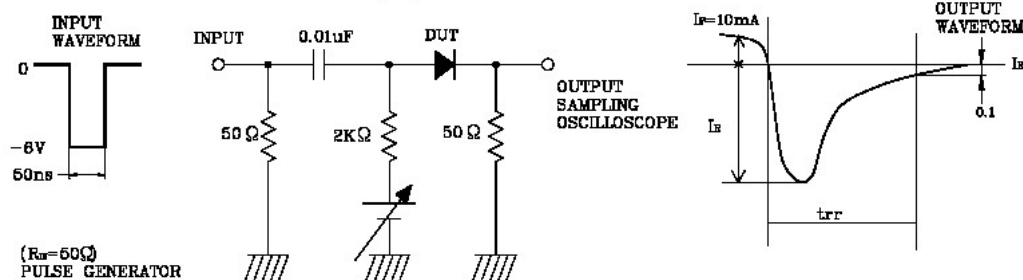


FIG. 5 - REVERSE RECOVERY TIME(t_{rr}) TEST CIRCUIT



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